

IN THE SPECIFICATION:

Please replace paragraph [0020] with the following amended paragraph:

[0020] Figure 8 is a partial cross-sectional view of the [[a]] substrate in a processing position in relation to the substrate supports described herein;

Please replace paragraph [0037] with the following amended paragraph:

[0037] Referring to Figures 5 and 6, the [[The]] capture ring 120 includes an arcuate base plate 202 having an inner perimeter 207 defining a bore 206 therein. A plurality of substrate supports, such as substrate supports 204, 205, are disposed on the inner perimeter 207. The substrate supports 204, 205 and the base plate 202 define a substrate receiving area. The substrate supports 204, 205 and the base plate 202 are adapted to mate with the substrate supports 118 on the cover ring [[mate]] when contacting the cover ring 116 and the capture ring 120 and define a planar substrate receiving surface for processing. The lift pins 114 move the capture ring 120 vertically above the cover ring 116 during substrate transfer and then lower the capture ring onto the cover ring 116 for processing. The whole assembly 115 may then be moved vertically within the chamber 160.

Please replace paragraph [0043] with the following amended paragraph:

[0043] Figure 8 is a partial cross sectional view of the substrate 222 disposed on the substrate supporting ridge 225 of the cathode 112 and within a perimeter defined by the substrate supports 118 of the cover ring 116 and substrate supports 204, 205 of the capture ring ~~of the substrate 222~~ in a processing position. The substrate supporting ridge 225 of the cathode 112 defines a supporting surface on which the substrate is supported during processing. A space 170 is defined between the substrate supporting ridge 225 and a lower surface of a substrate 222 when the substrate 222 is received on the substrate supporting ridge 225. A backside gas can be flowed into the space 170 during processing to facilitate thermal conduction and to prevent process gases from

being introduced behind the substrate 222. The backside gas can be delivered into the space 170, for example, by the backside gas line 188 disposed in the pedestal 116 from a remotely located backside gas source 190 through gas portals (not shown) to the surface of the cathode 112.

Please replace paragraph [0048] with the following amended paragraph:

[0048] The supporting apparatus and substrate handler blade 300 described above may also be taken advantage of in a substrate processing system 410 providing support for a substrate. The substrate processing system 410 may include a transfer chamber 414, at least one processing chamber 160 with a substrate support member 100 with a support surface and a capture ring coupled to the support surface, the capture ring adapted to receive a substrate, and a substrate handler 418 disposed in the transfer chamber 414. The substrate handler 418 preferably has a substrate handler blade 300 described above. The process chambers are preferably plasma etch chambers.